

TIM1414-7-253

1. RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

| CHARACTERISTICS | SYMBOL | CONDITION | MIN. | TYP. | MAX. | UNIT |
|---------------------------------------|--------------|---------------------------|------|------|------|------|
| Output Power at 1dB Compression Point | P1dB(1) | VDS= 9V f=13.75GHz | 37.0 | 38.0 | — | dBm |
| Output Power at 1dB Compression Point | P1dB(2) | VDS= 9V f=14.0-14.5GHz | 37.5 | 38.5 | — | |
| Power Gain at 1dB Compression Point | G1dB | VDS= 9V | 5.0 | 6.0 | — | dB |
| Drain Current | IDS | f=13.75-14.5GHz | — | 2.25 | 2.75 | A |
| Power Added Efficiency | η_{add} | | — | 23 | — | % |

DataSheet4U.com

2. ELECTRICAL CHARACTERISTICS (Ta= 25°C)

| CHARACTERISTICS | SYMBOL | CONDITION | MIN. | TYP. | MAX. | UNIT |
|-------------------------------|----------|----------------------|------|------|------|------|
| Transconductance | gm | VDS= 3V IDS= 2.4A | — | 1500 | — | mS |
| Pinch-off Voltage | VGSoff | VDS= 3V IDS= 72mA | -1.5 | -3.0 | -4.5 | V |
| Saturated Drain Current | IDSS | VDS= 3V VGS=0V | — | 5.0 | 5.7 | A |
| Gate-Source Breakdown Voltage | VGSO | IGS= -72 μ A | -5 | — | — | V |
| Thermal Resistance | Rth(c-c) | Channel to Case | — | 3.0 | 3.7 | °C/W |

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